| Substitute for form 1449A/PTO<br>**INFORMATION DISCLOSURE STATEMENT BY APPLICANT** | | |
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| | Application Number | 10/719,663 |
| | Filing Date | November 20, 2003 |
| | First Named Inventor | Faris |
| | Group Art Unit | 2818 |
| | Examiner Name | Nguyen, Dao H |
| Sheet 1 of 6 | Attorney Docket Number | Reveo-0202USAAON00 |

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| | Examiner Name | Nguyen, Dao H |
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| | Examiner Name | Nguyen, Dao H |
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| | Examiner Name | Nguyen, Dao H |
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